

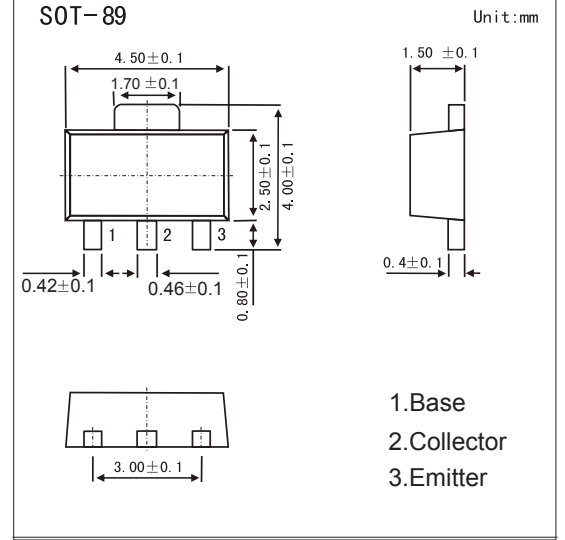
SOT-89 Plastic-Encapsulate Transistors

Features

- Small Flat Package
- High Transition Frequency
- High Voltage
- Complementary to 2SA1201
- NPN Transistors

MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	120	V
Collector - Emitter Voltage	V_{CE0}	120	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_C	800	mA
Base Current	I_B	160	
Collector Power Dissipation	P_C	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to 150	

PACKAGE INFORMATION

Device	Package	Shipping
2SC2881	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 100\mu A, I_E = 0$	120			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 10mA, I_B = 0$	120			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100\mu A, I_C = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 120V, I_E = 0$			0.1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$			1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 50mA$			1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = 5V, I_C = 0.5A$			1	
DC current gain	h_{FE}	$V_{CE} = 5V, I_C = 100mA$	80		240	
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$			30	pF
Transition frequency	f_T	$V_{CE} = 5V, I_C = 100mA$		120		MHz

Classification of h_{FE}

Type	2SC2881-O	2SC2881-Y
Range	80-160	120-240
Marking	CO*	CY*



RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

